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(54) Title: METHODS OF FORMING MICROELECTRONIC DEVICES, AND RELATED MICROELECTRONIC DEVICES, AND ELECTRONIC SYSTEMS

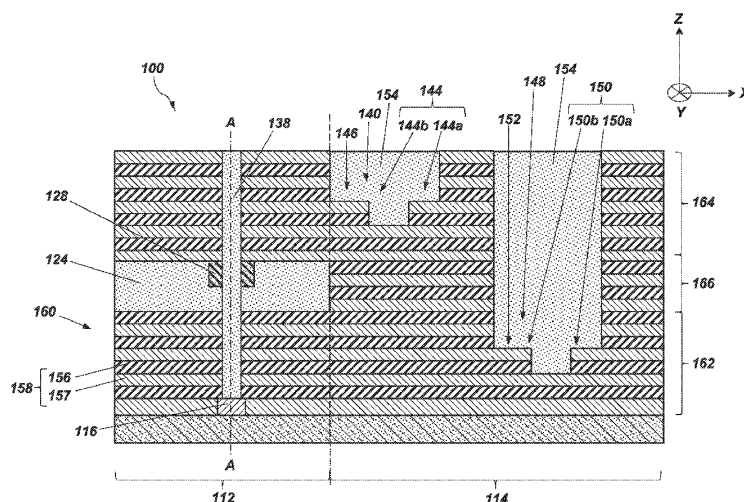


FIG. 10A

(57) **Abstract:** A microelectronic device comprises a microelectronic device structure having a memory array region and a staircase region. The microelectronic device structure comprises a stack structure having tiers each comprising a conductive structure and an insulative structure; staircase structures confined within the staircase region and having steps comprising edges of the tiers of the stack structure within the deck and the additional deck; and semiconductive pillar structures confined within the memory array region and extending through the stack structures. The stack structure comprises a deck comprising a group of the tiers; an additional deck overlying the deck and comprising an additional group of the tiers; and an interdeck section between the deck and the additional deck and comprising a dielectric structure confined within the memory array region, and another group of the tiers within vertical boundaries of the dielectric structure and confined within of the staircase region.

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- *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

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